

N-channel TrenchMOS standard level FET 5 October 2012

Product data sheet

Product profile 1.

1.1 General description

Standard level N-channel MOSFET in a SOT404 package using TrenchMOS technology. This product has been designed and qualified to AEC Q101 standard for use in high performance automotive applications.

1.2 Features and benefits

- AEC Q101 compliant •
- Repetitive avalanche rated •
- Suitable for thermally demanding environments due to 175 °C rating
- True standard level gate with VGS(th) rating of greater than 1V at 175 °C •

1.3 Applications

- 12V, 24V and 48V Automotive systems
- Motors, lamps and solenoid control •
- Start-Stop micro-hybrid applications
- Transmission control
- Ultra high performance power switching •

1.4 Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C		-	-	100	V
I _D	drain current	V _{GS} = 10 V; T _{mb} = 25 °C; <u>Fig. 1</u>		-	-	34	А
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 2</u>		-	-	96	W
Static charac	cteristics	·					
R _{DSon}	drain-source on-state resistance	V _{GS} = 10 V; I _D = 10 A; T _j = 25 °C; <u>Fig. 11</u>		-	24.3	31	mΩ
Dynamic characteristics							
Q _{GD}	gate-drain charge	V _{GS} = 10 V; I _D = 10 A; V _{DS} = 80 V; T _j = 25 °C; <u>Fig. 13; Fig. 14</u>		-	10.7	-	nC

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2. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	mb	D
2	D	drain		
3	S	source		G-UF44
mb	D	mounting base; connected to drain	D2PAK (SOT404)	mbb076 S

3. Ordering information

Table 3. Ordering information							
Type number	Package						
	Name	Description	Version				
BUK7631-100E	D2PAK	plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped)	SOT404				

4. Marking

Table 4. Marking codes	
Type number	Marking code
BUK7631-100E	BUK7631-100E

5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C	-	100	V
V _{DGR}	drain-gate voltage	R _{GS} = 20 kΩ	-	100	V
V _{GS}	gate-source voltage	T _j = 175 °C; DC	-20	20	V
I _D	drain current	T _{mb} = 25 °C; V _{GS} = 10 V; <u>Fig. 1</u>	-	34	А
		T _{mb} = 100 °C; V _{GS} = 10 V; <u>Fig. 1</u>	-	24	А
I _{DM}	peak drain current	T_{mb} = 25 °C; pulsed; $t_p \le 10 \ \mu$ s; Fig. 4	-	136	А
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 2</u>	-	96	W
T _{stg}	storage temperature		-55	175	°C
Tj	junction temperature		-55	175	°C
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Symbol	Parameter	Conditions		Min	Max	Unit
Source-drain	Source-drain diode					_
I _S	source current	T _{mb} = 25 °C		-	34	А
I _{SM}	peak source current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$		-	136	А
Avalanche ru	Avalanche ruggedness					
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	$\label{eq:ID} \begin{array}{l} {\sf I}_{D} = 34 \; {\sf A}; \; {\sf V}_{sup} \le 100 \; {\sf V}; \; {\sf R}_{GS} = 50 \; \Omega; \\ {\sf V}_{GS} = 10 \; {\sf V}; \; {\sf T}_{j(init)} = 25 \; {\rm ^\circ C}; \; unclamped; \\ \hline {\sf Fig. 3} \end{array}$	[1][2]	-	39.4	mJ

Single-pulse avalanche rating limited by maximum junction temperature of 175 °C.
Refer to application note AN10273 for further information.

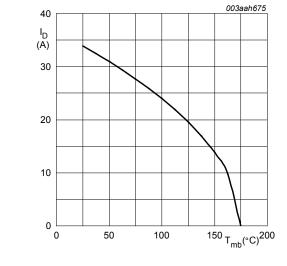


Fig. 1. Continuous drain current as a function of mounting base temperature

 $V_{GS} \ge 10V$

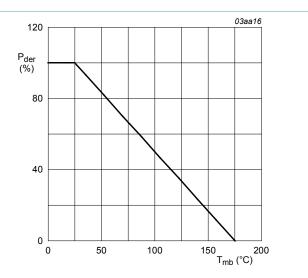
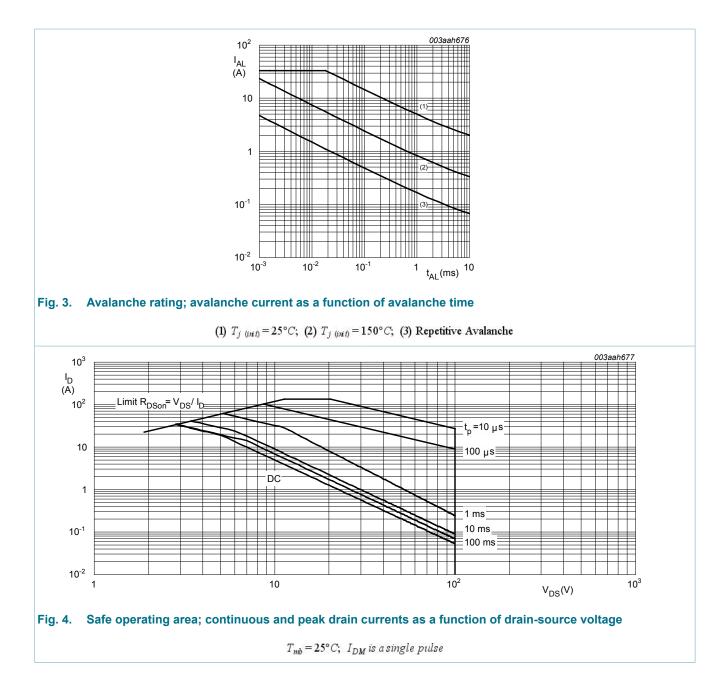


Fig. 2. Normalized total power dissipation as a function of mounting base temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100 \%$$

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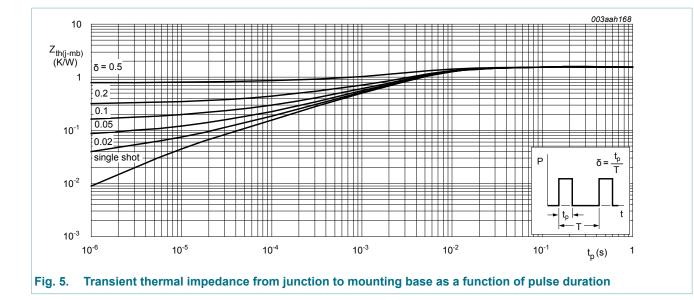
Thermal characteristics 6.

Symbol	Parameter	Conditions	N	lin	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	Fig. <u>5</u>	-		-	1.56	K/W
R _{th(j-a)}	thermal resistance from junction to ambient	minimum footprint ; mounted on a printed-circuit board	-		50	-	K/W

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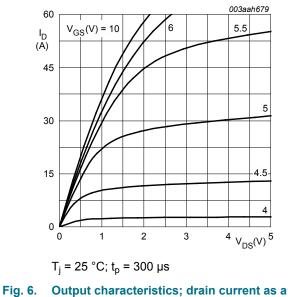


Characteristics 7.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics	· · ·	I			_
V _{(BR)DSS}	drain-source	I_D = 250 µA; V_{GS} = 0 V; T_j = 25 °C	100	-	-	V
	breakdown voltage	I_D = 250 µA; V_{GS} = 0 V; T_j = -55 °C	90	-	-	V
V _{GS(th)}	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C};$ Fig. 9; Fig. 10	2.4	3	4	V
	I _D = 1 mA; V _{DS} = V _{GS} ; T _j = 175 °C; <u>Fig. 9</u>	5 50 50 j	1	-	-	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C};$ Fig. 9	-	-	4.5	V
I _{DSS}	drain leakage current	V_{DS} = 100 V; V_{GS} = 0 V; T_j = 25 °C	-	0.04	1	μA
		V_{DS} = 100 V; V_{GS} = 0 V; T_j = 175 °C	-	-	500	μA
I _{GSS}	gate leakage current	V_{GS} = 20 V; V_{DS} = 0 V; T_j = 25 °C	-	2	100	nA
		V _{GS} = -20 V; V _{DS} = 0 V; T _j = 25 °C	-	2	100	nA
R _{DSon}	drain-source on-state resistance	V _{GS} = 10 V; I _D = 10 A; T _j = 25 °C; Fig. 11	-	24.3	31	mΩ
		V _{GS} = 10 V; I _D = 10 A; T _j = 175 °C; Fig. 11; Fig. 12	-	-	84	mΩ
Dynamic cl	naracteristics	· · ·	- I			
Q _{G(tot)}	total gate charge	I_D = 10 A; V_{DS} = 80 V; V_{GS} = 10 V;	-	29.4	-	nC
Q _{GS}	gate-source charge	T _j = 25 °C; <u>Fig. 13; Fig. 14</u>	-	5.1	-	nC
Q _{GD}	gate-drain charge		-	10.7	-	nC

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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
C _{iss}	input capacitance	V _{GS} = 0 V; V _{DS} = 25 V; f = 1 MHz; T _j = 25 °C; <u>Fig. 15</u>	-	1303	1738	pF
C _{oss}	output capacitance	V_{GS} = 0 V; V_{DS} = 25 V; f = 1 MHz;	-	145	174	pF
C _{rss}	reverse transfer capacitance	T _j = 25 °C; <u>Fig. 15</u>	-	105	144	pF
t _{d(on)}	turn-on delay time	V_{DS} = 80 V; R_L = 5 Ω ; V_{GS} = 10 V;	-	8.4	-	ns
t _r	rise time	$R_{G(ext)} = 5 \Omega$	-	18.2	-	ns
t _{d(off)}	turn-off delay time		-	22.1	-	ns
t _f	fall time		-	20	-	ns
L _D	internal drain inductance	from upper edge of mounting base to centre of die	-	2.5	-	nH
L _S	internal source inductance	measured from source lead to source bond pad ; T_j = 25 °C	-	7.5	-	nH
Source-dra	in diode					
V _{SD}	source-drain voltage	I _S = 10 A; V _{GS} = 0 V; T _j = 25 °C; <u>Fig. 16</u>	-	0.83	1.2	V
t _{rr}	reverse recovery time	I_{S} = 10 A; dI _S /dt = -100 A/µs; V _{GS} = 0 V;	-	36	-	ns
Q _r	recovered charge	V _{DS} = 25 V	-	58.7	-	nC





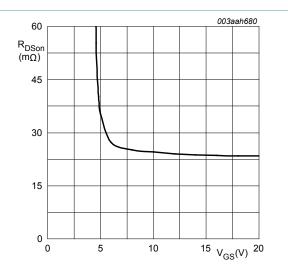
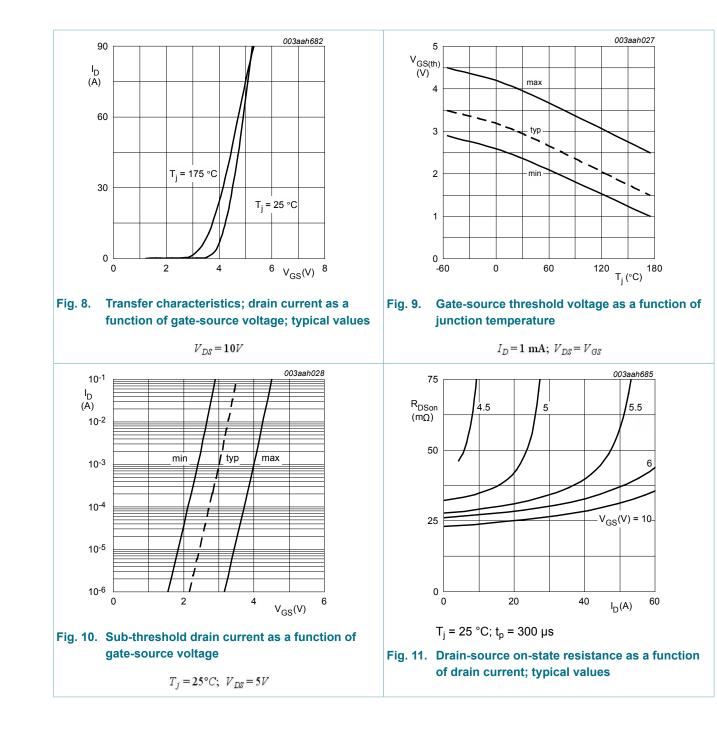


Fig. 7. Drain-source on-state resistance as a function of gate-source voltage; typical values

 $T_j = 25^{\circ}C; \ I_D = 10A$

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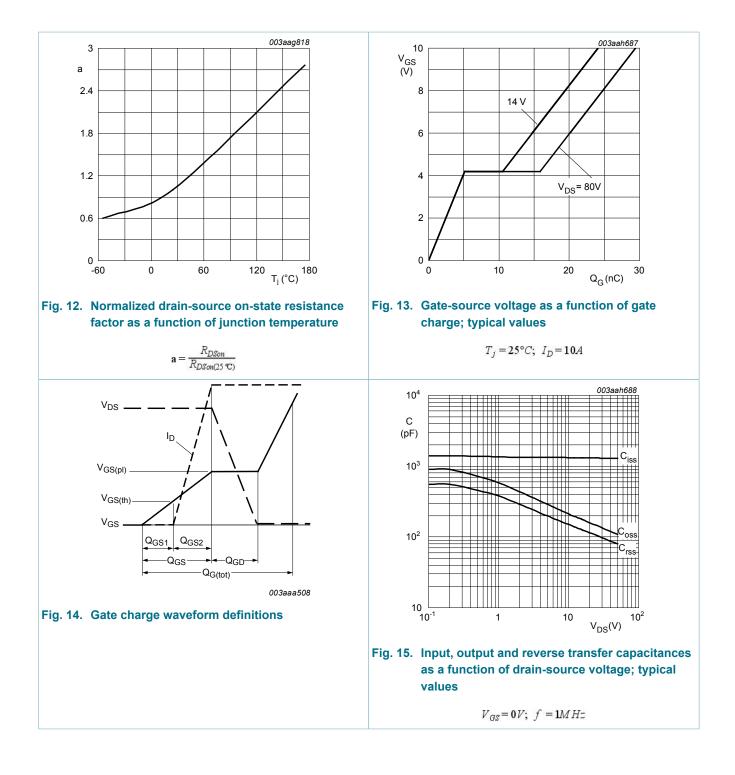


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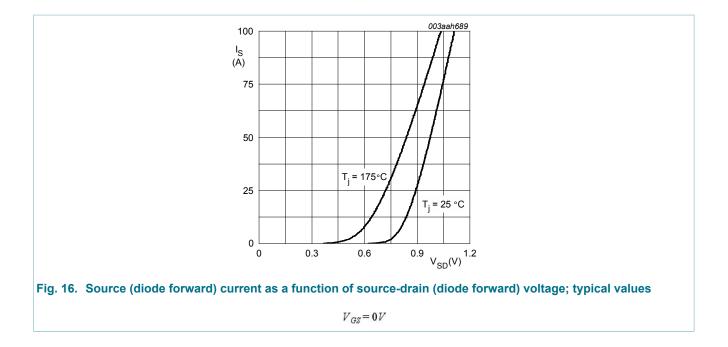
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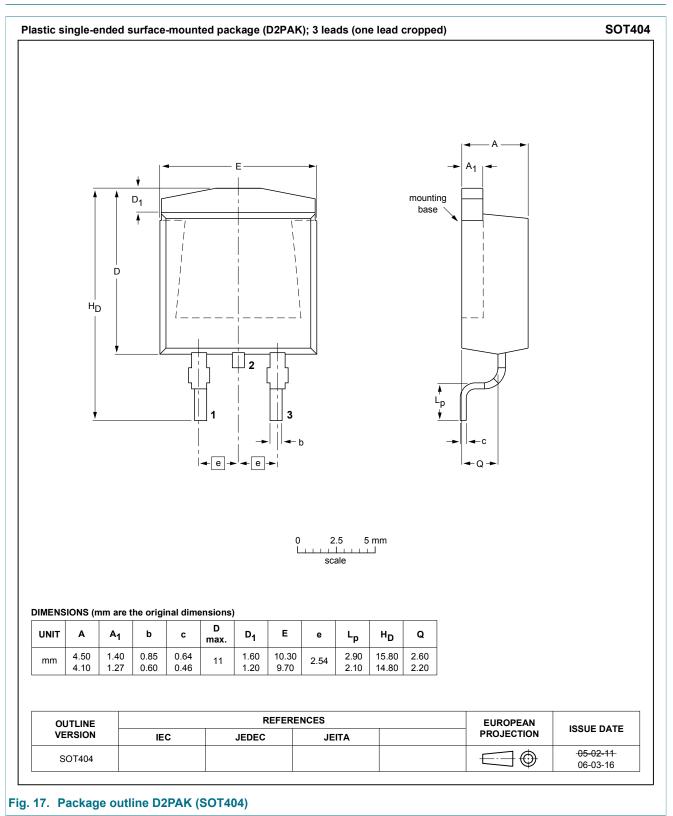
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8. Package outline



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9. Legal information

9.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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[2] The term 'short data sheet' is explained in section "Definitions".

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